

S8050 NPN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY AMPLIFIER

- * Complement to S8050
- * Collector Current :Ic=500mA
- * High Total Power Dissipation: p_C=625mW

ABSOLUTE MAXIMUM RATINGS at Tamb=25°C

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{cb0}	40	V
Collector-Emitter Voltage	V _{ceo}	25	V
Emitter-Base Voltage	V _{eb0}	6	V
Collector Current	I _c	500	mA
Collector Dissipation	P _C	625	m W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55~150	°C

ELECTRICAL CHARACTERISTICS at Tamb=25°C

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{cb0}	40			V	I _c =100uA I _e =0
Collector-Emitter Breakdown Voltage	BV _{ceo}	25			V	I _c =1mA I _b =0
Emitter-Base Breakdown Voltage	BV _{eb0}	6			V	I _e =100uA I _c =0
Collector Cutoff Current	I _{cb0}			100	nA	V _{cb} =25V I _e =0
Emitter Cutoff Current	I _{eb0}			100	nA	V _{eb} =3v I _c =0
DC Current Gain	Hfe ₁	85	160	400		V _{ce} =1V I _c =50mA
DC Current Gain	Hfe ₂	30				V _{ce} =1V I _c =500mA
Collector-Emitter Saturation Voltage	V _{ce(sat)}		0.18	0.6	V	I _c =500mA I _b =50mA
Base-Emitter Saturation Voltage	V _{be(sat)}		0.95	1.2	V	I _c =500mA I _b =50mA
Base-Emitter On Voltage	V _{be(on)}	0.6	0.67	0.7	V	V _{ce} =1V I _c =10mA

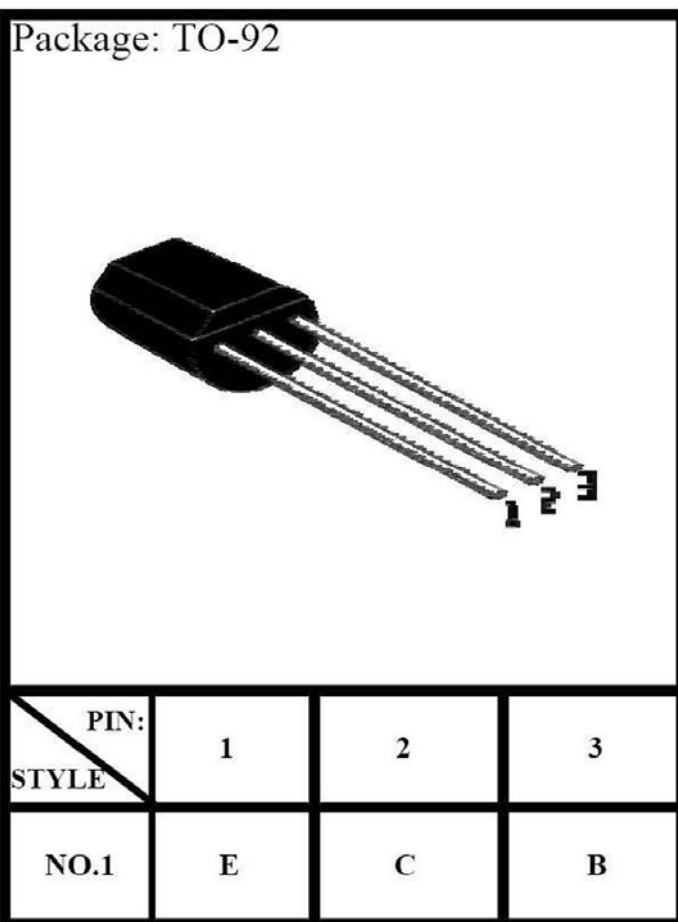
CLASSIFICATION HFE

Classification	B	C	D
Hfe ₁	85-160	120-200	160-400



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